ROHM Co.,Ltd.
21 Saiin Mizosaki-cho, Ukyo-ku,
Kyoto 615-8585 Japan
TEL:+81-75-311-2121 FAX:+81-75-315-0172
http://www.rohm.com

Notification of Product/Process Change

Doc. No.: 3022002

This letter intends as a formal notification of change to products which are currently supplied by ROHM Co., Ltd.

ROHM Co., Ltd. requires customers to provide acknowledgment of the receipt of this notification within 30 days from the date of this notice. Lack of acknowledgment of this notice within 30 days is considered as acceptance of the change.

After acknowledgement of the customer, lack of additional response within 90 day period constitutes acceptance of the change according to JEDEC Standard J-STD-046.

Your understanding and cooperation would be highly appreciated.

Issue Date: September 1, 2022

Title of change	Application for additional approval of GEM's TO-252 transistor products assembly plant (Hefei)	
Identification of change	Products manufactured at the Hefei Plant can be identified by dot marking. (Please refer to the 4M change materials)	
Affected product(s)	Manufacturer part number	Customer part number
	Please refer to the attachment.	
Detailed description of change	Before	After
	Assembly plant : GEM's Shanghai plant (China)	Assembly plant : GEM's Shanghai plant (China) GEM's Hefei plant (China)
Reason for change	In order to ensure a stable supply in the future, we will apply for additional approval for the Hefei Plant.	
Anticipated impact on form, fit, function, quality or reliability	Since the materials, mounted die and manufacturing equipments are same as Shanghai plant use, we judge that the product electrical characteristics and quality are the same.	
Planned first ship date	October 1 (Consultation required after approval)	
Qualification plan schedule, results and samples	If required, please contact the local ROHM sales office or the authorized distributor.	
Comments	-	
Supplier contact	Please contact the local ROHM sales office or the authorized distributor.	
Notes		

Difference between Shanghai and Hefei plants (5M+1E change point)

Appl No.3022002

Item	Shanghai Plant	Hefei Plant	Variation	Remarks
	TO-252			
Name of production plant	GEM Electronics (Shanghai) Co.,Ltd.	GEM Electronics (Hefei) Co.,Ltd.	having	The production site was changed to another plant of GEM.
The country of origin	China		None	The country of origin is the same in China.
Man	Workers certified by the contractor		None	Education is conducted in the same program. No difference in competence.
Material	Wafers are supplied by ROHM		None	Uses the same elements. No difference in elements.
	Materials used by contractors		None	Use of identical assembly materials. (Manufacturer, part number, and production location are also identical)
Machine	Use of contractor's equipment		None	The same manufacturer's machine is used. No difference with the production machine.
Method	Contractor's work standards		None	Use the same work standards. No difference in production methods.
Measurement	Measured with a program determined by ROHM		None	Use the same program/measuring device. No difference in measurement process.
Environment	Production process clean room management Temperature: 20 to 28°C Humidity: 40-60% RH Clean room class: 10,000		None	The same management is implemented. No difference with respect to environment.

➢ Production equipment, materials, production method and education program used at the Hefei plant are identical to those used at the Shanghai plant. The only change is a change in production location.

Difference between Shanghai and Hefei Plants (Product Change Points)

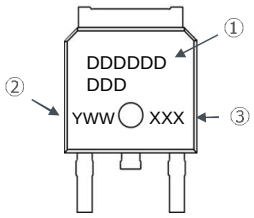
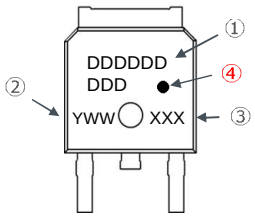
Appl No.3022002

Item	Shanghai Plant / Hefei Plant	Variation	Remarks
	TO-252		
Absolute maximum ratings	Identity (No difference)	None	For details, please refer to the individual datasheets.
Electrical Characteristics	Identity (No difference)	None	For details, please refer to the individual datasheets.
Dimensions	Identity (No difference)	None	For details, please refer to the individual datasheets.
Reference Land Pattern	Identity (No difference)	None	For details, please refer to the individual datasheets.
Terminal processing	Identity (Electroplating : Sn)	None	Generation method/material/thickness No difference.
Marking method	Identity (Scanning laser marking)	None	Printing method/size/font No difference.
Contents of Marking	Identity (No difference in description)	None	For details of the description, please refer to the Appendix of【Identification(Traceability)】section.
Packing	Identity (No difference in taping and packaging specifications)	None	For details, please refer to the individual datasheets.
Label	Identity (No difference in description)	None	For details of the description, please refer to the Appendix of【Identification(Traceability)】section.

➢ Product electrical Characteristics, specification and dimensions are same, there is no difference.

Identification (Traceability) of Shanghai and Hefei Plants

Appl No.3022002

Item	Shanghai Plant	Hefei Plant	Variation	Remarks
	TO-252			
Marking			having	The production plant can be identified by the marking (④ with or without dots). 【Without dots: Made at Shanghai Plant】, 【With dots: Made at Hefei Plant】
	①: Indicate part number ②: Y=end of production year, WW=week of production. ③: XXX = Serial No.			
Label (Lot No.)			having	The last two digits of the Lot No. can be used to identify the production plant. 【EG: made in Shanghai plant】 【FG: made in Hefei plant】. (Country of origin: China, no difference)
	Lot No. end = EG	Lot No. end = FG		

信頼性試験結果 Reliability Test Result		ローム株式会社 パワーデバイス品質管理課 ROHM Co., Ltd. Power Device Quality Control Dept.		作成 Designed	承認 Approved
作成日(DATE)	2022年6月2日 02-Jun-22	品名(product)	Bipolar Transistor		Appl No.3022002
管理No.(Serial No.)	BIP-TO-252(Bip)_1	PKG(Type)	TO-252(Bip)		

1. 試験結果(TEST RESULT)

試験項目 (TEST ITEM)	試験条件 (TEST CONDITION)	準拠規格 (STANDARD)	n[pcs] (Sample QTY.)	Pn[pcs] (NG QTY.)
はんだ耐熱性 Soldering heat resistance	260±5℃、10秒、リフロー方式　2回 260±5℃、10sec.、Reflow method 2times	JESD22-A111	22	0
	260±5℃、10秒、はんだ槽 260±5℃、10sec.、Solder-bath		22	0
	350±10℃、3秒、手付け 350±10℃、3sec.、Hand soldering		22	0
はんだ付け性 Solderability	245±5℃ ,3秒、リフロー方式 245±5℃ ,3sec.、Reflow　method	J-STD-002	22	0
	245±5℃、3秒、はんだ槽 245±5℃、3sec.、Solder-bath	JESD22-B102	22	0
温度サイクル Temperature cycle	-55±5℃⟷150±5℃　200サイクル -55±5℃⟷150±5℃　200cycles	JESD22-A104	22	0
高温高湿逆バイアス High temp. high humidity reverse bias	85±2℃, 85±5%RH, 規定のバイアス, 1000時間 85±2℃, 85±5%RH, specified bias ,1000hours	JESD22-A101	22	0
飽和蒸気加圧　PCT Pressure cooker test	121±2℃、100%RH、203kPa、100時間 121±2℃、100%RH、203kPa、100hours	JESD22-A102	22	0
高温逆バイアス High temperature reverse bias	Ta=Tstg max, 規定のバイアス、1000時間 Ta=Tstg max., specified bias、1000hours	JESD22-A108	22	0
高温保存 High temperature storage	Tstg max., 1000時間 Tstg max., 1000hours	-	22	0
低温保存 Low temperature storage	Tstg min., 1000時間 Tstg min., 1000hours	-	22	0
断続動作 Intermittent operation life	Ta=25℃±5℃ ,ON 130s/OFF 230s P_C max, 10000 サイクル Ta=25℃±5℃ ,ON 130s/OFF 230s P_C max, 10000 cycles	EIAJ ED-4701/100 Test Method 106	22	0
端子強度(引っ張り) Lead strength (lead pull)	製品固定状態で軸方向荷重10N、10±1sec保持. Sample body fixed, pulling lead axis direction、10N、10±1sec.	JEITA ED-4701/400 Test Method 401	22	0
負荷寿命 Load Life	25℃、Pc=Pc max.　1000時間 25℃、Pc=Pc max　1000hours	-	22	0
熱衝撃 Thermal shock	0℃ ～ 100℃、100サイクル 0℃ ～ 100℃、100cycles	-	22	0

2. 測定項目及び故障判定基準(FAILURE CRITERIA)

測定項目 (ITEM)	測定条件 (CONDITION)	故障判定基準 (CRITERIA)	
しゃ断電流　: ICBO Cutoff current　: ICBO	仕様書条件による Per　specification	規格値の2倍以内 Within two times of the standard value.	
しゃ断電流　: IEBO Cutoff current　: IEBO	仕様書条件による Per　specification	規格値の2倍以内 Within two times of the standard value.	
増幅率 : hFE DC current gain : hFE	仕様書条件による Per specification	初期値に対する変化率　±20% Changing rate of ±20%	
外観 Physical	目視 Visual check	著しい変化のないこと No outstanding change in physical.	
はんだ付け性 Solderability	目視 Visual check	リフロー方式 Reflow Soldering	端子先端部を除く端面にフィレットが形成されること Immersed surfase, other than the end of pin as cut-surface, must be covered by solder.
		はんだ槽 Solder-bath	電極部の95%以上がはんだで覆われていること More than 95% of the electrode must be covered with solder.

3. 判定結果(JUDGEMENT)

各試験項目とも不具合の発生は認められておりません。
No failure is observed from　each test item.

BIP(SOT-428(CPT3))

信頼性試験結果 Reliability Test Result		ローム株式会社 パワーデバイス品質管理課 ROHM Co., Ltd. Power Device Quality Control Dept.		作成 Designed	承認 Approved
作成日(DATE)	2022年6月2日 02-Jun-22	品名(product)	MOS Appl No.3022002		
管理No.(Serial No.)	MOS-TO-252_1	形名, PKG(Type)	TO-252		

1. 試験結果(TEST RESULT)

試験項目 (TEST ITEM)	試験条件 (TEST CONDITION)	準拠規格 (STANDARD)	n[pcs] (Sample QTY.)	Pn[pcs] (NG QTY.)
はんだ耐熱性 Soldering heat resistance	260±5℃, 10秒, リフロー方式, 2回 260±5℃, 10sec., Reflow method 2times	JESD22-A111	22	0
	260±5℃, 10秒, はんだ槽 260±5℃, 10sec., Solder-bath		22	0
	350±10℃, 3秒, 手付け 350±10℃, 3sec., Hand soldering		22	0
はんだ付け性 Solderability	245±5℃, 3秒, リフロー方式 245±5℃, 3sec., Reflow method	J-STD-002	22	0
	245±5℃, 3秒, はんだ槽 245±5℃, 3sec., Solder-bath	JESD22-B102	22	0
温度サイクル Temperature cycle	-55±5℃←→150±5℃ 200サイクル -55±5℃←→150±5℃ 200cycles	JESD22-A104	22	0
高温高湿逆バイアス High temp. high humidity reverse bias	85±2℃, 85±5%RH, 規定のバイアス, 1000時間 85±2℃, 85±5%RH, specified bias, 1000hours	JESD22-A101	22	0
飽和蒸気加圧 PCT Pressure cooker test	121±2℃, 100%RH, 203kPa, 100時間 121±2℃, 100%RH, 203kPa, 100hours	JESD22-A102	22	0
高温逆バイアス High temperature reverse bias	Ta=Tstg max. 規定のバイアス、1000時間 Ta=Tstg max., specified bias, 1000hours	JESD22-A108	22	0
高温ゲートバイアス High temperature gate bias	Ta=Tstg max, V_{GSS}(max),1000時間 Ta=Tstg max, V_{GSS}(max), , 1000hours	JESD22-A108	22	0
高温保存 High temperature storage	Tstg max., 1000時間 Tstg max., 1000hours	-	22	0
低温保存 Low temperature storage	Tstg min., 1000時間 Tstg min., 1000hours	-	22	0
断続動作 Intermittent operation life	Ta=25℃±5℃, ON 130s/OFF 230s P_D max, 10000 サイクル Ta=25℃±5℃, ON 130s/OFF 230s P_D max, 10000 cycles	EIAJ ED-4701/100 Test Method 106	22	0
端子強度(引っ張り) Lead strength (lead pull)	製品固定状態で軸方向荷重10N, 10±1sec保持. Sample body fixed, pulling lead axis direction, 10N, 10±1sec.	JEITA ED-4701/400 Test Method 401	22	0
負荷寿命 Load Life	25℃, P_D=P_D max. 1000時間 25℃, P_D=P_D max 1000hours	-	22	0
熱衝撃 Thermal shock	0℃ ～ 100℃, 100サイクル 0℃ ～ 100℃, 100cycles	-	22	0

2. 測定項目及び故障判定基準(FAILURE CRITERIA)

測定項目 (ITEM)	測定条件 (CONDITION)	故障判定基準 (CRITERIA)	
ゲート漏れ電流 : IGSS Gate-Source Leakage : IGSS	仕様書条件による Per specification	規格値の2倍以内 Within the two times of the standard value.	
ドレイン遮断電流 : IDSS Zero Gate Voltage Drain Current : IDSS	仕様書条件による Per specification	規格値の2倍以内 Within the two times of the standard value.	
順電圧ｱﾄﾞﾐﾀﾝｽ : | Yfs | Forward Transfer Admittance : |Yfs|	仕様書条件による Per specification	初期値に対する変化率 ±20% Changing rate of ±20%	
外観 Physical	目視 Visual check	著しい変化のないこと No outstanding change in physical.	
はんだ付け性 Solderability	目視 Visual check	リフロー方式 Reflow Soldering	端子先端部を除く端面にフィレットが形成されること Immersed surface, other than the end of pin as cut-surface, must be covered by solder.
		はんだ槽 Solder-bath	電極部の95%以上がはんだで覆われていること More than 95% of the electrode must be covered with solder.

3. 判定結果(JUDGEMENT)

各試験項目とも不具合の発生は認められておりません。
No failure is observed from each test item.

MOS(TO-252)

No.	Target PN					Replacement PN		
	Level1	Internal PN	Rcmd Ctgry	Public (External) PN		Internal PN	Rcmd Ctgry	Public (External) PN
1	TO252G	2SAR572D3 TL1	0→2	2SAR572D3 TL1	→	2SAR572D38CATL1	0	2SAR572D3 TL1
2	TO252G	2SAR573D3 TL1	0→2	2SAR573D3 TL1	→	2SAR573D38CATL1	0	2SAR573D3 TL1
3	TO252G	2SAR574D3 TL1	0→2	2SAR574D3 TL1	→	2SAR574D38CATL1	0	2SAR574D3 TL1
4	TO252G	2SAR582D3 TL1	0→2	2SAR582D3 TL1	→	2SAR582D38CATL1	0	2SAR582D3 TL1
5	TO252G	2SAR583D3 TL1	0→2	2SAR583D3 TL1	→	2SAR583D38CATL1	0	2SAR583D3 TL1
6	TO252G	2SAR586D3 TL1	0→2	2SAR586D3 TL1	→	2SAR586D38CATL1	0	2SAR586D3 TL1
7	TO252G	2SAR587D3 TL1	0→2	2SAR587D3 TL1	→	2SAR587D38CATL1	0	2SAR587D3 TL1
8	TO252G	2SCR572D3 TL1	0→2	2SCR572D3 TL1	→	2SCR572D38CATL1	0	2SCR572D3 TL1
9	TO252G	2SCR573D3 TL1	0→2	2SCR573D3 TL1	→	2SCR573D38CATL1	0	2SCR573D3 TL1
10	TO252G	2SCR574D3 TL1	0→2	2SCR574D3 TL1	→	2SCR574D38CATL1	0	2SCR574D3 TL1
11	TO252G	2SCR582D3 TL1	0→2	2SCR582D3 TL1	→	2SCR582D38CATL1	0	2SCR582D3 TL1
12	TO252G	2SCR583D3 TL1	0→2	2SCR583D3 TL1	→	2SCR583D38CATL1	0	2SCR583D3 TL1
13	TO252G	2SCR586D3 TL1	0→2	2SCR586D3 TL1	→	2SCR586D38CATL1	0	2SCR586D3 TL1
14	TO252G	2SCR587D3 TL1	0→2	2SCR587D3 TL1	→	2SCR587D38CATL1	0	2SCR587D3 TL1
15	TO252G	RD3H045SP TL1	0→2	RD3H045SP TL1	→	RD3H045SP8AATL1	0	RD3H045SP TL1
16	TO252G	RD3H080SP TL1	0→2	RD3H080SP TL1	→	RD3H080SP8AATL1	0	RD3H080SP TL1
17	TO252G	RD3H160SP TL1	0→2	RD3H160SP TL1	→	RD3H160SP8AATL1	0	RD3H160SP TL1
18	TO252G	RD3L140SP TL1	0→2	RD3L140SP TL1	→	RD3L140SP8AATL1	0	RD3L140SP TL1
19	TO252G	RD3P130SP TL1	0→2	RD3P130SP TL1	→	RD3P130SP8AATL1	0	RD3P130SP TL1
20	TO252G	RD3H200SN TL1	0→2	RD3H200SN TL1	→	RD3H200SN8AATL1	0	RD3H200SN TL1
21	TO252G	RD3L050SN TL1	0→2	RD3L050SN TL1	→	RD3L050SN8AATL1	0	RD3L050SN TL1
22	TO252G	RD3L080SN TL1	0→2	RD3L080SN TL1	→	RD3L080SN8AATL1	0	RD3L080SN TL1
23	TO252G	RD3L150SN TL1	0→2	RD3L150SN TL1	→	RD3L150SN8AATL1	0	RD3L150SN TL1
24	TO252G	RD3L220SN TL1	0→2	RD3L220SN TL1	→	RD3L220SN8AATL1	0	RD3L220SN TL1
25	TO252G	RD3P050SN TL1	0→2	RD3P050SN TL1	→	RD3P050SN8AATL1	0	RD3P050SN TL1
26	TO252G	RD3P100SN TL1	0→2	RD3P100SN TL1	→	RD3P100SN8AATL1	0	RD3P100SN TL1
27	TO252G	RD3P175SN TL1	0→2	RD3P175SN TL1	→	RD3P175SN8AATL1	0	RD3P175SN TL1
28	TO252G	RD3P200SN TL1	0→2	RD3P200SN TL1	→	RD3P200SN8AATL1	0	RD3P200SN TL1
29	TO252G	RD3S075CN TL1	0→2	RD3S075CN TL1	→	RD3S075CN8CATL1	0	RD3S075CN TL1
30	TO252G	RD3S100CN TL1	0→2	RD3S100CN TL1	→	RD3S100CN8CATL1	0	RD3S100CN TL1
31	TO252G	RD3T050CN TL1	0→2	RD3T050CN TL1	→	RD3T050CN8CATL1	0	RD3T050CN TL1
32	TO252G	RD3T075CN TL1	0→2	RD3T075CN TL1	→	RD3T075CN8CATL1	0	RD3T075CN TL1
33	TO252G	RD3T100CN TL1	0→2	RD3T100CN TL1	→	RD3T100CN8CATL1	0	RD3T100CN TL1
34	TO252G	RD3U040CN TL1	0→2	RD3U040CN TL1	→	RD3U040CN8CATL1	0	RD3U040CN TL1
35	TO252G	RD3U060CN TL1	0→2	RD3U060CN TL1	→	RD3U060CN8CATL1	0	RD3U060CN TL1
36	TO252G	RD3U080CN TL1	0→2	RD3U080CN TL1	→	RD3U080CN8CATL1	0	RD3U080CN TL1
37	TO252G	RD3G03BBG TL1	0→2	RD3G03BBG TL1	→	RD3G03BBG8SATL1	0	RD3G03BBG TL1
38	TO252G	RD3G07BBG TL1	0→2	RD3G07BBG TL1	→	RD3G07BBG8SATL1	0	RD3G07BBG TL1
39	TO252G	RD3L03BBG TL1	0→2	RD3L03BBG TL1	→	RD3L03BBG8SATL1	0	RD3L03BBG TL1
40	TO252G	RD3L07BBG TL1	0→2	RD3L07BBG TL1	→	RD3L07BBG8SATL1	0	RD3L07BBG TL1
41	TO252G	RD3P03BBH TL1	5→2	RD3P03BBH TL1	→	RD3P03BBH8SATL1	0	RD3P03BBH TL1
42	TO252G	RD3P07BBH TL1	5→2	RD3P07BBH TL1	→	RD3P07BBH8SATL1	0	RD3P07BBH TL1
43	TO252G	RD3R02BBH TL1	5→2	RD3R02BBH TL1	→	RD3R02BBH8SATL1	0	RD3R02BBH TL1
44	TO252G	RD3R05BBH TL1	5→2	RD3R05BBH TL1	→	RD3R05BBH8SATL1	0	RD3R05BBH TL1
45	TO252G	RD3G01BAT TL1	0→2	RD3G01BAT TL1	→	RD3G01BAT8SATL1	0	RD3G01BAT TL1
46	TO252G	RD3G03BAT TL1	0→2	RD3G03BAT TL1	→	RD3G03BAT8SATL1	0	RD3G03BAT TL1
47	TO252G	RD3G07BAT TL1	0→2	RD3G07BAT TL1	→	RD3G07BAT8SATL1	0	RD3G07BAT TL1
48	TO252G	RD3L01BAT TL1	0→2	RD3L01BAT TL1	→	RD3L01BAT8SATL1	0	RD3L01BAT TL1
49	TO252G	RD3L03BAT TL1	0→2	RD3L03BAT TL1	→	RD3L03BAT8SATL1	0	RD3L03BAT TL1
50	TO252G	RD3L07BAT TL1	0→2	RD3L07BAT TL1	→	RD3L07BAT8SATL1	0	RD3L07BAT TL1
51	TO252G	RD3P01BAT TL1	0→2	RD3P01BAT TL1	→	RD3P01BAT8SATL1	0	RD3P01BAT TL1
52	TO252G	RD3P02BAT TL1	0→2	RD3P02BAT TL1	→	RD3P02BAT8SATL1	0	RD3P02BAT TL1
53	TO252G	RD3P05BAT TL1	0→2	RD3P05BAT TL1	→	RD3P05BAT8SATL1	0	RD3P05BAT TL1
54	TO252G	RD3W023DN TL1	1→2	RD3W023DN TL1	→	RD3W023DN8CATL1	0	RD3W023DN TL1

☆ The following product numbers are not applicable due to special circumstances. Please confirm this list.

For the items listed below, we will consider the application again after another priority application is completed.
Thank you for your understanding.

No.	Level1	Not applicable Internal PN	Rcmd Ctgry	Rrmarks	
1	TO252G	R6002END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6 process）
2	TO252G	R6004END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6 process）
3	TO252G	R6007END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6 process）
4	TO252G	R6009END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6 process）
5	TO252G	R6011END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6 process）
6	TO252G	R6502END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H1 process）
7	TO252G	R6504END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H1 process）
8	TO252G	R6507END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H1 process）
9	TO252G	R6509END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H1 process）
10	TO252G	R6511END3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H1 process）
11	TO252G	R6504KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6HS process）
12	TO252G	R6507KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6HS process）
13	TO252G	R6509KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6HS process）
14	TO252G	R6511KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6HS process）
15	TO252G	R8001KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
16	TO252G	R8002KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
17	TO252G	R8003KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
18	TO252G	R8006KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
19	TO252G	R6003KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
20	TO252G	R6004KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
21	TO252G	R6006KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
22	TO252G	R6007KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
23	TO252G	R6009KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
24	TO252G	R6011KND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
25	TO252G	R6011KND3 TR1	0	Not applicable	As another application is given priority, this application will be postponed.（C6H2 process）
26	TO252G	R6003JND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2 process）
27	TO252G	R6004JND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（PR2 process）
28	TO252G	R6006JND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（PR2 process）
29	TO252G	R6007JND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（PR2 process）
30	TO252G	R6009JND3 TL1	0	Not applicable	As another application is given priority, this application will be postponed.（PR2 process）
31	TO252G	R6004RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
32	TO252G	R6007RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
33	TO252G	R6009RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
34	TO252G	R6504RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
35	TO252G	R6507RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
36	TO252G	R6509RND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR2S process）
37	TO252G	R6013VND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（PR4 process）
38	TO252G	R6010YND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（SJ7 process）
39	TO252G	R6014YND3 TL1	5	Not applicable	As another application is given priority, this application will be postponed.（SJ7 process）
40	TO252G	R5205CND3 TL1	1	Not applicable	For products that do not expand sales (SJ1 process)
41	TO252G	R5207AND3 TL1	1	Not applicable	For products that do not expand sales (SJ1 process)
42	TO252G	RD3L06BGN TL1	5	Not applicable	UN4 : Under development item (To be registered on the premise of Shanghai/Hefei)
43	TO252G	RD3L08CGN TL1	5	Not applicable	UN4 : Under development item (To be registered on the premise of Shanghai/Hefei)
44	TO252G	RD3R04BBH TL1	5	Not applicable	UN4 : Under development item (To be registered on the premise of Shanghai/Hefei)
45	TO252G	2SCR573D39GUTL1	2	Not applicable	For special product item
46	TO252G	RD3P050SNM80TL1	2	Not applicable	For special product item